



SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

SFT1341 — P-Channel Silicon MOSFET — General-Purpose Switching Device Applications

Features

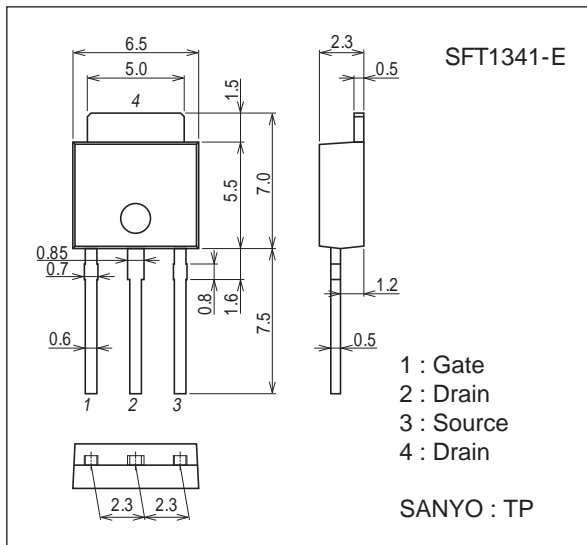
- 1.8V drive
- Protection diode in

Specifications

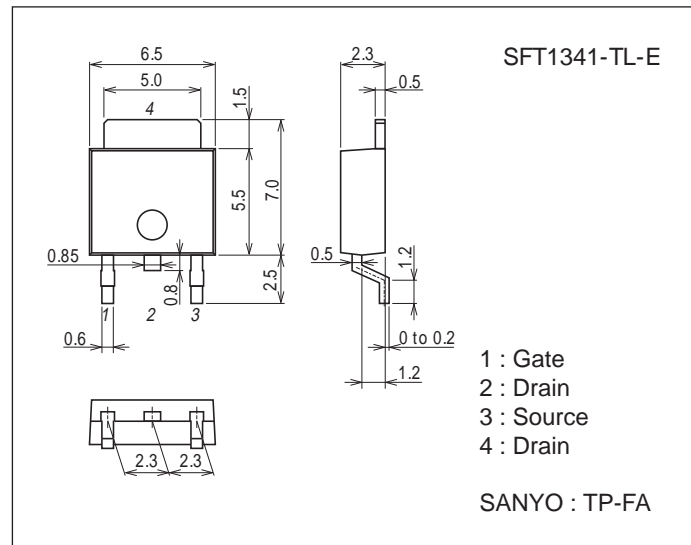
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		-40	V
Gate-to-Source Voltage	V _{GSS}		±10	V
Drain Current (DC)	I _D		-10	A
Drain Current (PW≤10μs)	I _{DP}	PW≤10μs, duty cycle≤1%	-40	A
Allowable Power Dissipation	P _D		1.0	W
		T _c =25°C	15	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Package Dimensions unit : mm (typ)
7518-004



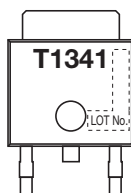
Package Dimensions unit : mm (typ)
7003-004



Product & Package Information

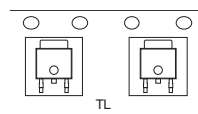
- Package : TP
- JEITA, JEDEC : SC-64, TO-251
- Minimum Packing Quantity : 500 pcs./bag

Marking (TP, TP-FA)

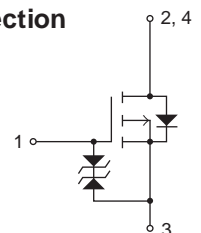


- Package : TP-FA
- JEITA, JEDEC : SC-63, TO-252
- Minimum Packing Quantity : 700 pcs./reel

Packing Type (TP-FA) : TL



Electrical Connection

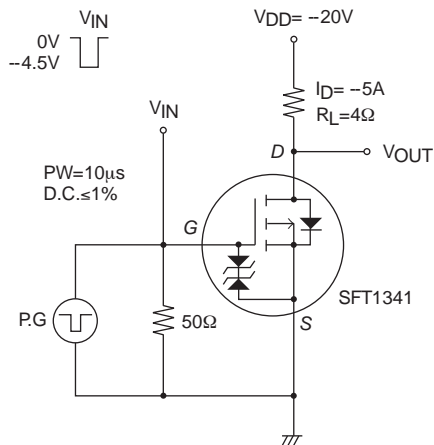


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Electrical Characteristics at Ta=25°C

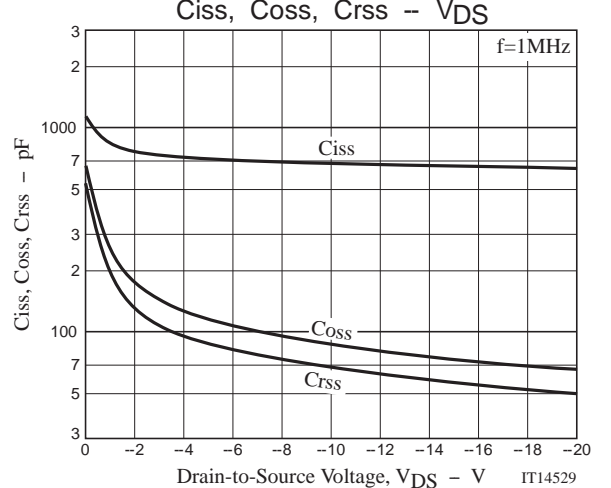
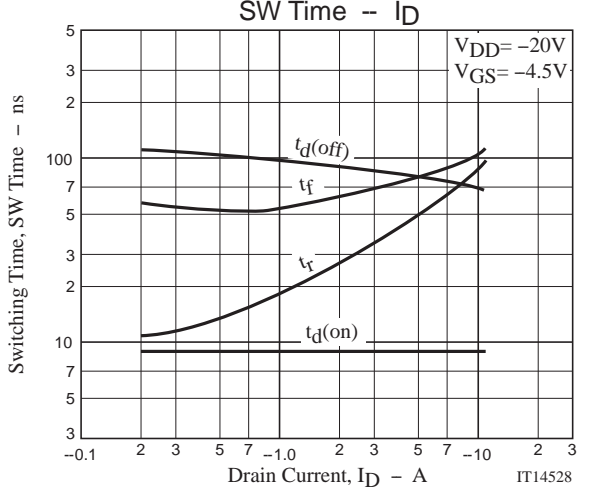
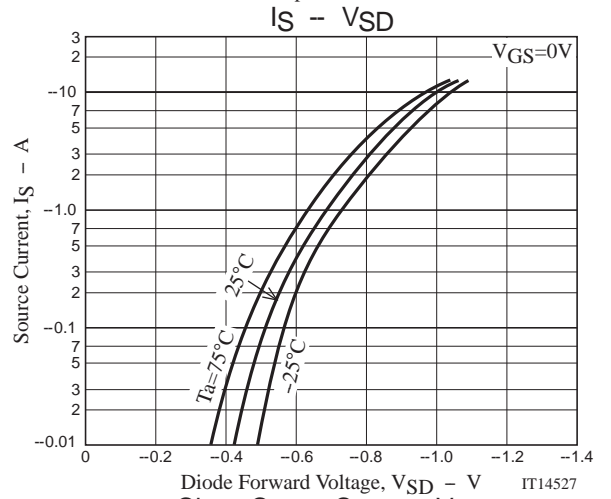
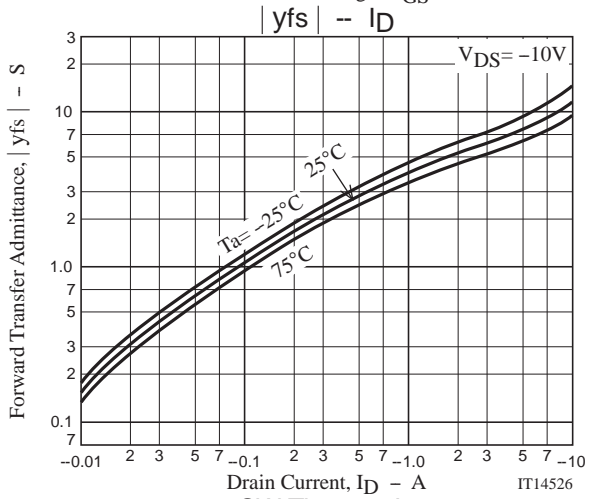
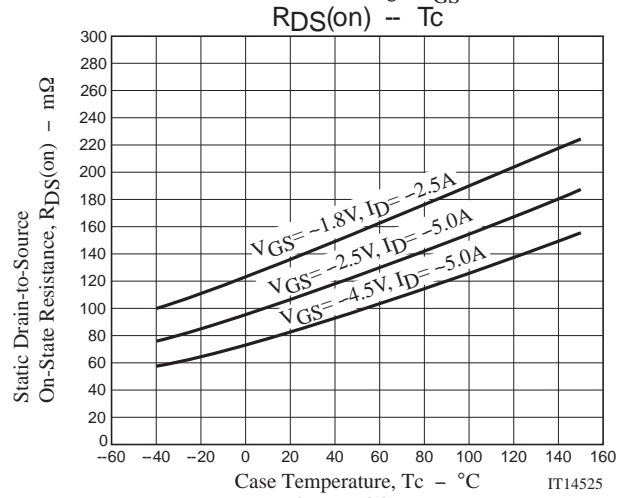
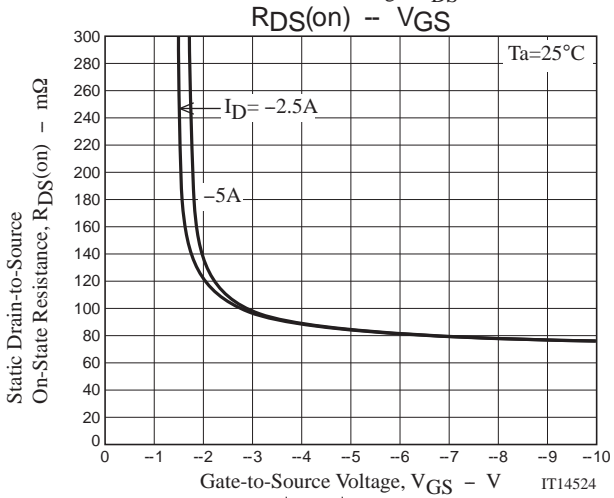
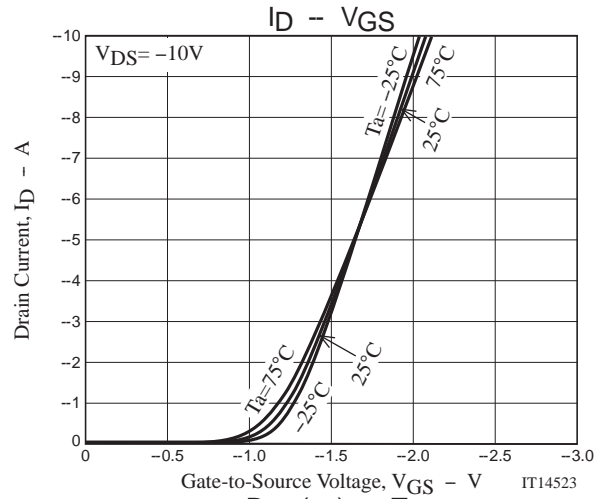
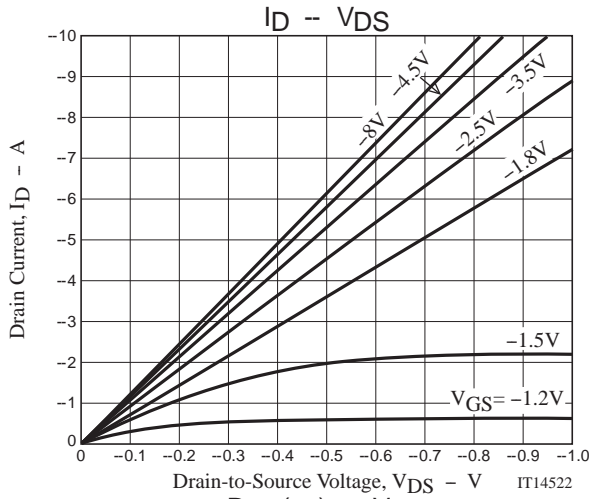
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-40			V
Zero-Gate Voltage Drain Current	IDSS	VDS=-40V, VGS=0V			-1	μA
Gate-to-Source Leakage Current	IGSS	VGS=±8V, VDS=0V			±10	μA
Cutoff Voltage	VGS(off)	VDS=-10V, ID=-1mA	-0.4		-1.4	V
Forward Transfer Admittance	yfs	VDS=-10V, ID=-5A	4.6	7.7		S
Static Drain-to-Source On-State Resistance	RDS(on)1	ID=-5A, VGS=-4.5V		86	112	mΩ
	RDS(on)2	ID=-5A, VGS=-2.5V		110	154	mΩ
	RDS(on)3	ID=-2.5A, VGS=-1.8V		140	210	mΩ
Input Capacitance	Ciss			650		pF
Output Capacitance	Coss	VDS=-20V, f=1MHz		65		pF
Reverse Transfer Capacitance	Crss			50		pF
Turn-ON Delay Time	td(on)	See specified Test Circuit.		9.0		ns
Rise Time	tr			50		ns
Turn-OFF Delay Time	td(off)			81		ns
Fall Time	tf			80		ns
Total Gate Charge	Qg				8.0	
Gate-to-Source Charge	Qgs	VDS=-20V, VGS=-4.5V, ID=-10A		1.4		nC
Gate-to-Drain "Miller" Charge	Qgd			2.5		nC
Diode Forward Voltage	VSD		IS=-10A, VGS=0V		-1.0	-1.5

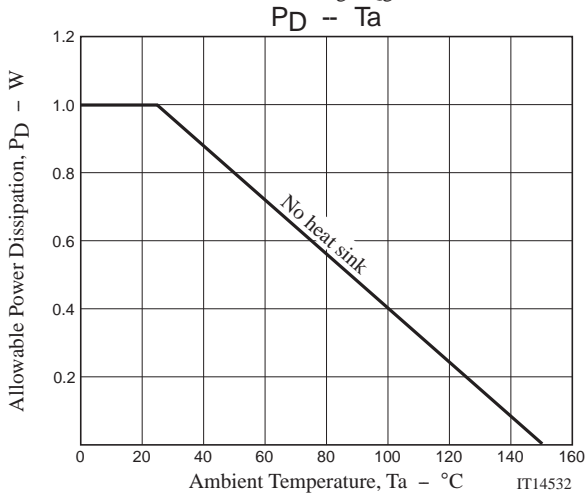
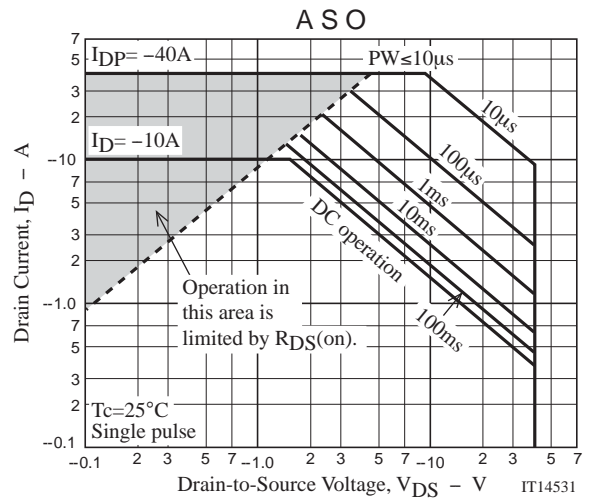
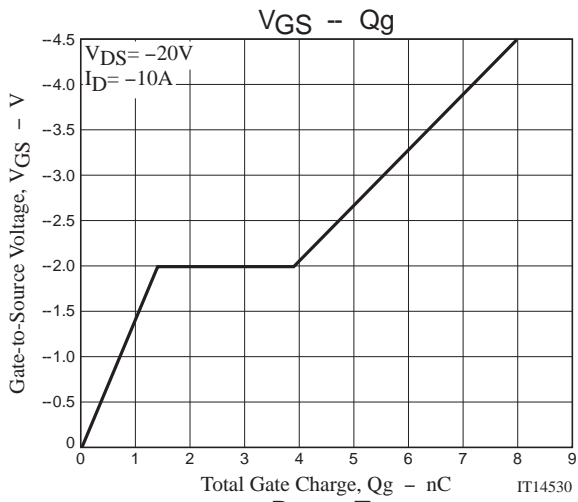
Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo
SFT1341-E	TP	500pcs./bag	Pb Free
SFT1341-TL-E	TP-FA	700pcs./reel	





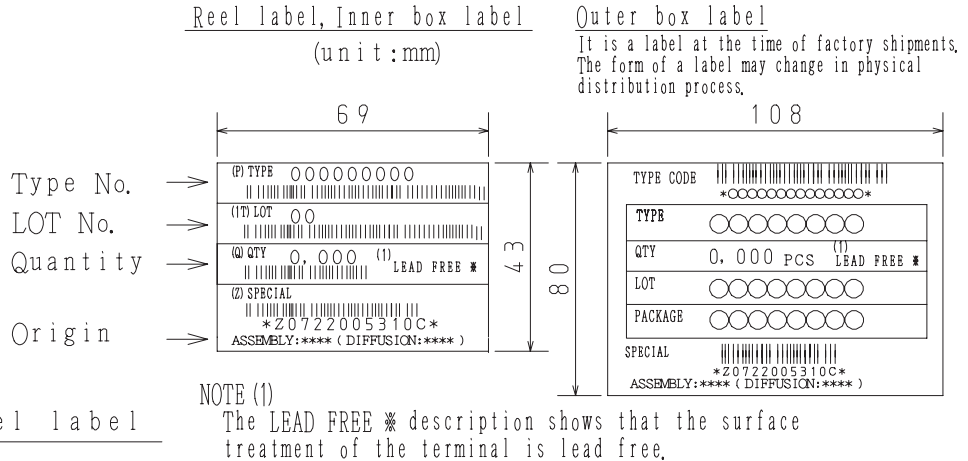
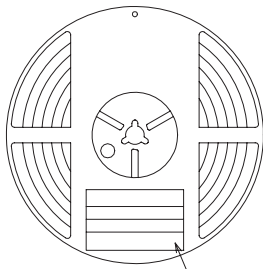
Taping Specification

SFT1341-TL-E

Packing Format

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
TP-FA	TP	700	2,100	12,600	3 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

Packing method



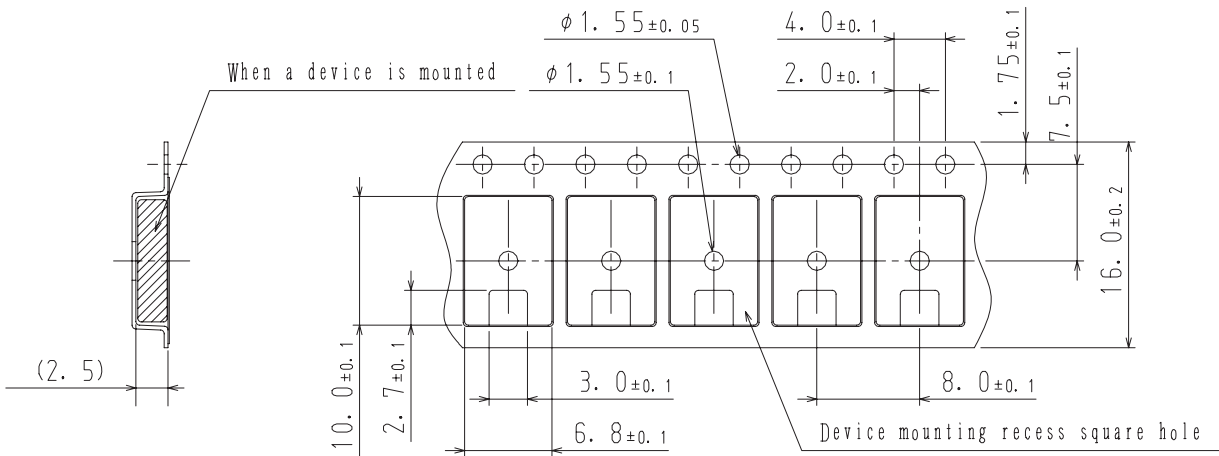
NOTE (1)

The LEAD FREE # description shows that the surface treatment of the terminal is lead free.

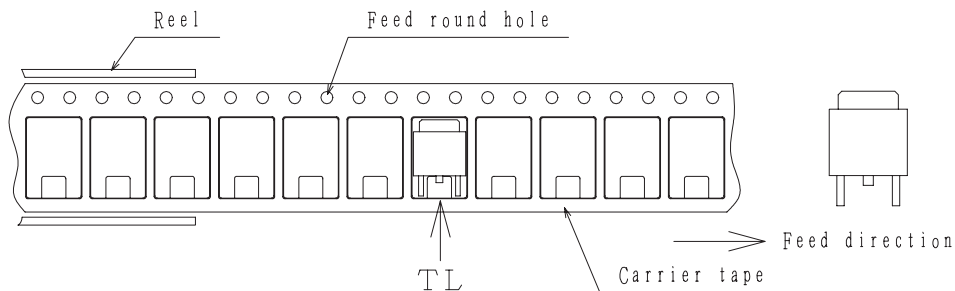
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

Taping configuration

1. Carrier tape size (unit:mm)



2. Device placement direction

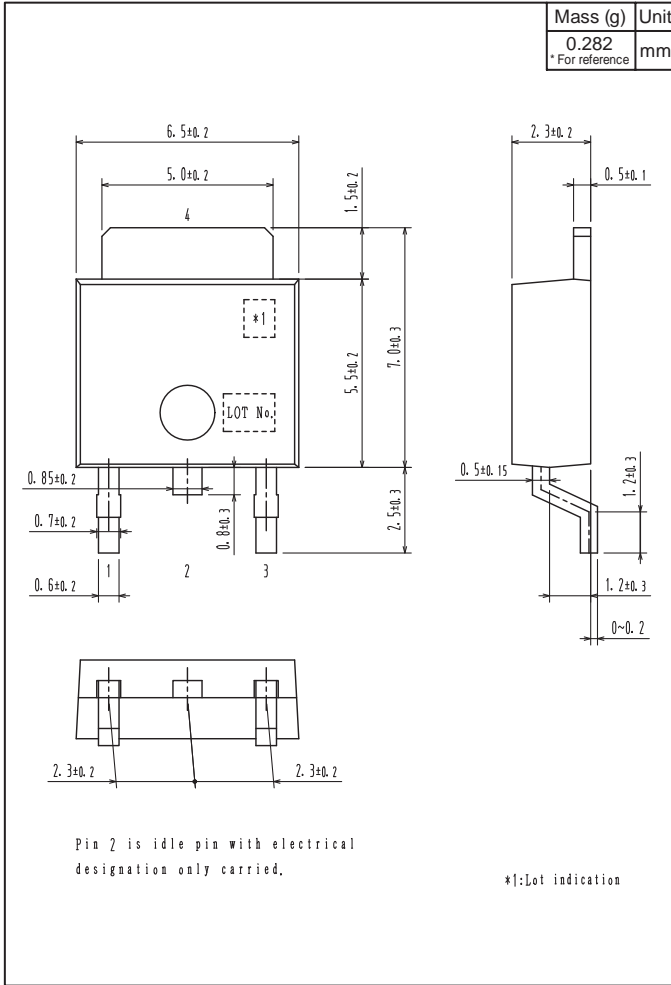


Those with one electrode terminal on the feed hole side.....TL

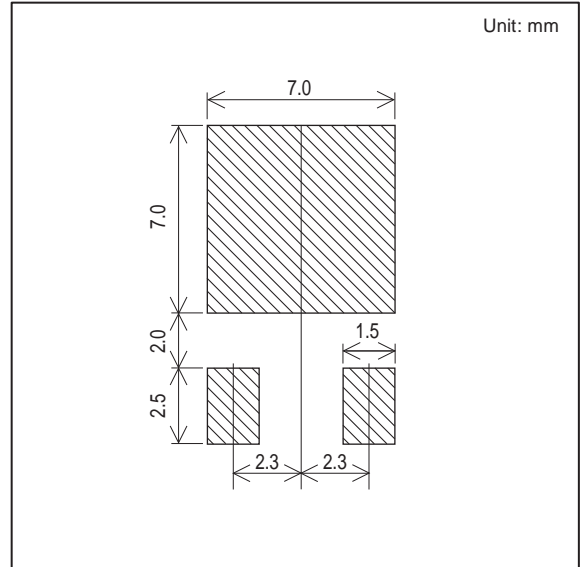
SFT1341

Outline Drawing

SFT1341-TL-E



Land Pattern Example



SFT1341

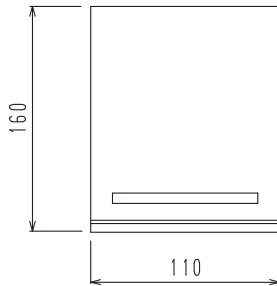
Bag Packing Specification

SFT1341-E

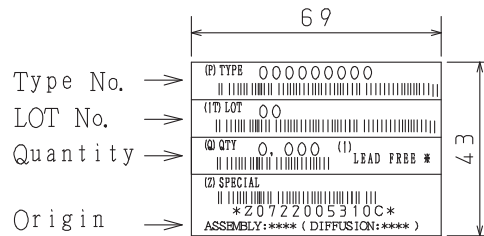
1. Packing Format

Package Name	Maximum Number of devices contained (pcs)			
	Bag	Inner box	Outer box	
TP	500	B-1	A-1	A-2
		10,000	50,000	30,000
Packing format (Dimensions:mm (external))				
		Inner box	Outer box	
		B-1	A-1	A-2
		445×225×55	470×250×300	470×250×190

2. Bag dimensions (unit:mm)



3. Bag label, Inner box label (unit:mm)



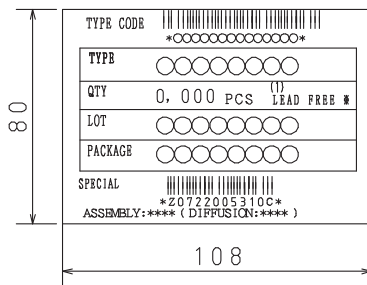
4. Outer box label (unit:mm)

It is a label at the time of factory shipments.
The form of a label may change in physical
distribution process.

NOTE (1)

The LEAD FREE * description shows that the
surface treatment of the terminal is lead free.

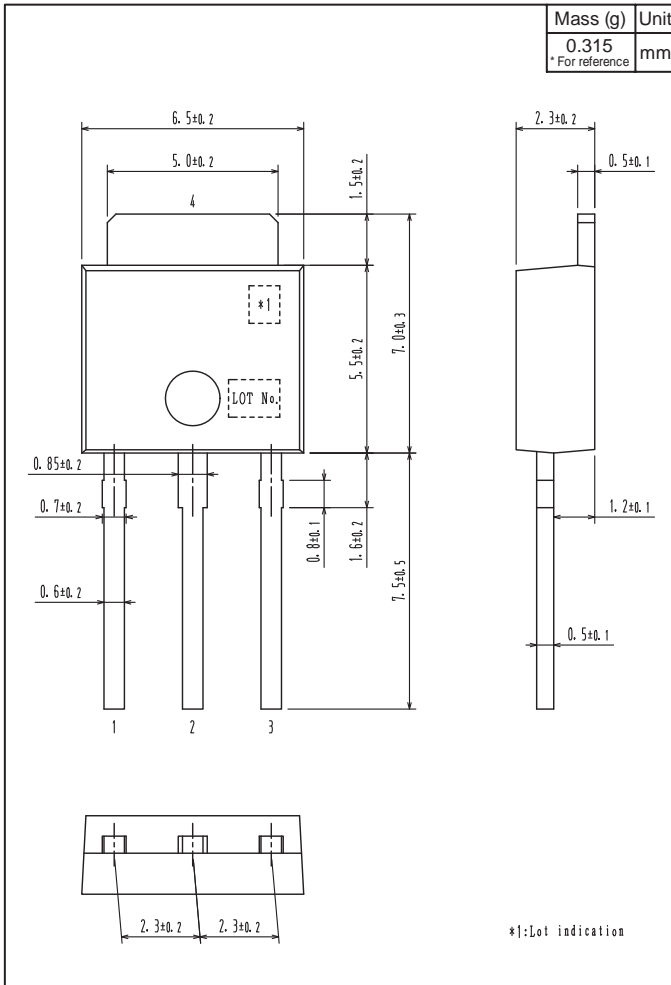
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3



SFT1341

Outline Drawing

SFT1341-E



Note on usage : Since the SFT1341 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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